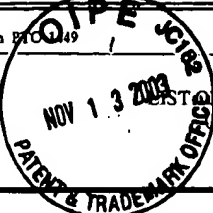


Form PTO-1349 SEP 30 2004 U.S. DEPARTMENT OF COMMERCE PATENT & TRADEMARK OFFICE		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-1531		SERIAL NO. 09/755,673		
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U.S. PATENT DOCUMENTS								
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K.N.	AB	5,985,731	11/99	Weng et al	438	396	Aug. 17, 1998	
K.N.	AC	6,395,650	05/02	Callegari et al	438	785	Oct. 23, 2000	
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
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ATTY. DOCKET NO.
MI22-1531

SERIAL NO.
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APPLICANT
Micon Technology, Inc.

FILING DATE
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2823

PTO
09/15/81

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Khuemnguyen

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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)					APPLICANT Micron Technology, Inc.			
					FILING DATE Filed Herewith 01/05/61		GROUP 2823	
U.S. PATENT DOCUMENTS								
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U.S. PATENT DOCUMENTS						
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